

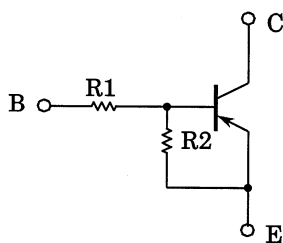
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2101FV, RN2102FV, RN2103FV RN2104FV, RN2105FV, RN2106FV

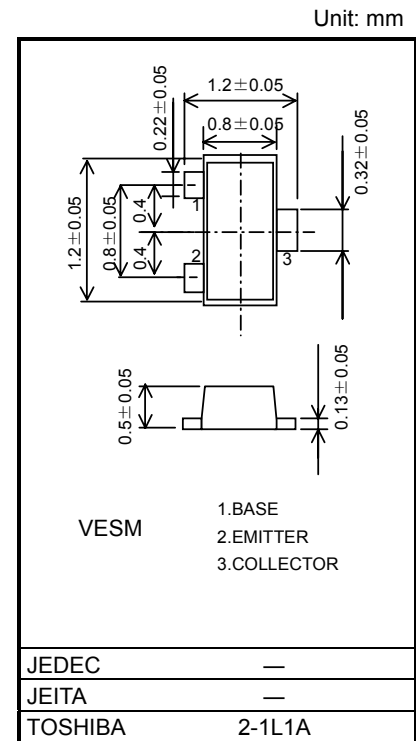
Switching, Inverter Circuit, Interface Circuit
and Driver Circuit Applications

- Built-in bias resistors
- Simplified circuit design
- Reduced quantity of parts and manufacturing process
- Complementary to RN1101FV~RN1106FV

Equivalent Circuit and Bias Resister Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2101FV	4.7	4.7
RN2102FV	10	10
RN2103FV	22	22
RN2104FV	47	47
RN2105FV	2.2	47
RN2106FV	4.7	47

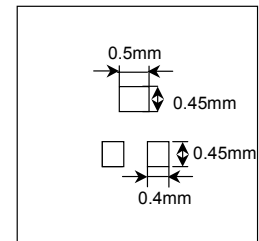


Weight: 0.0015g (typ.)

Maximum Ratings (Ta = 25°C)

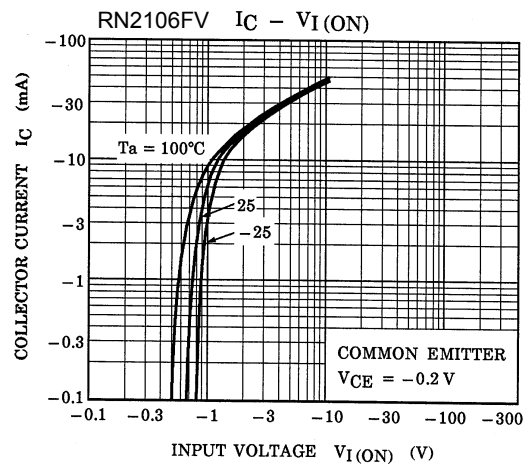
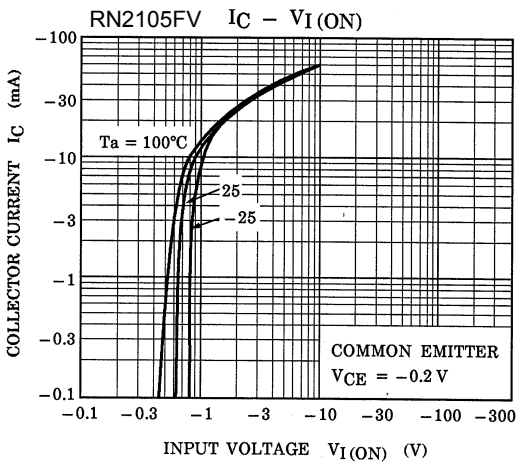
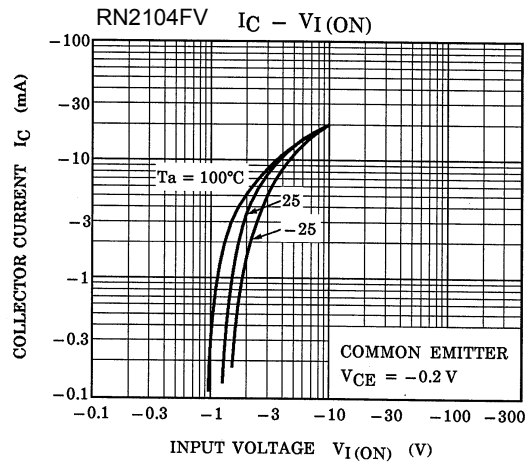
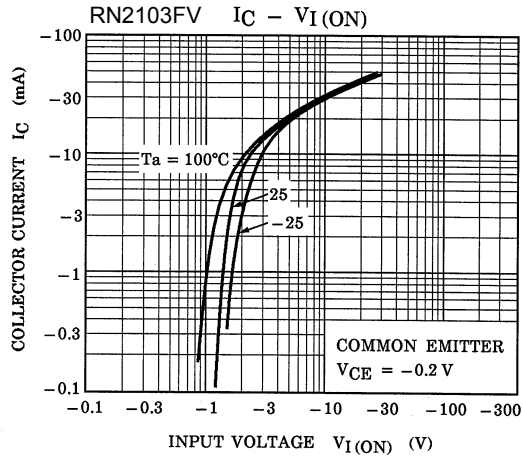
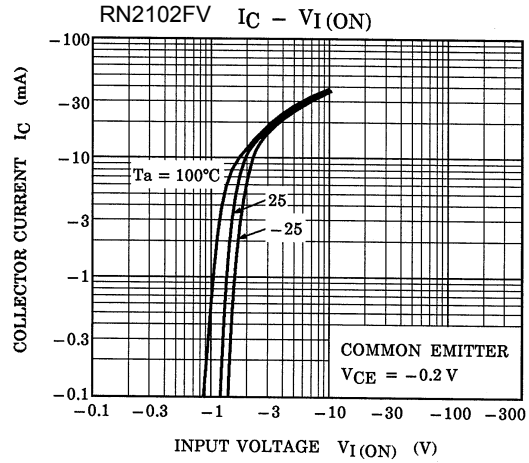
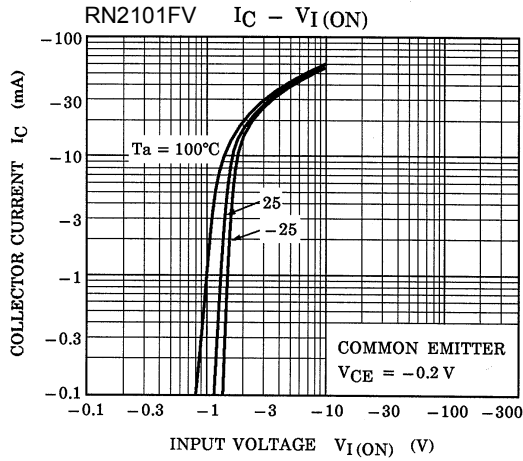
Characteristic	Symbol	Rating	Unit	
Collector-base voltage	RN2101FV~2106FV	V_{CB0}	-50	V
Collector-emitter voltage				
Emitter-base voltage	RN2101FV~2104FV	V_{EBO}	-10	V
	RN2105FV, 2106FV		-5	
Collector current	RN2101FV~2106FV	I_C	-100	mA
Collector power dissipation		P_C (Note)	150	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55~150	°C

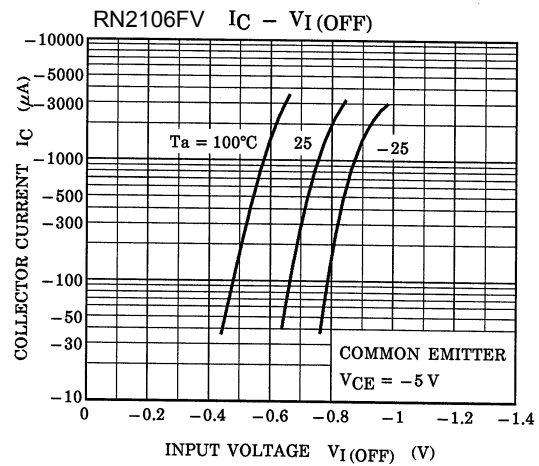
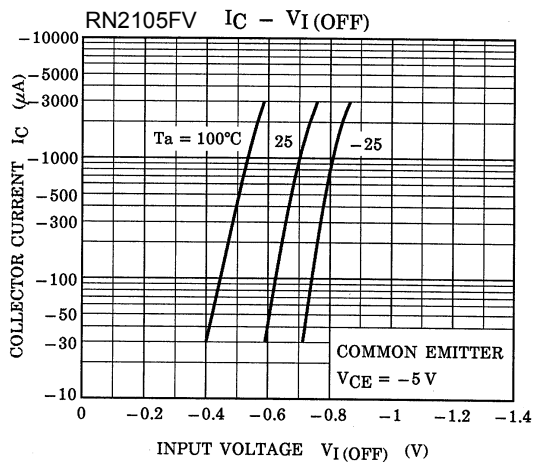
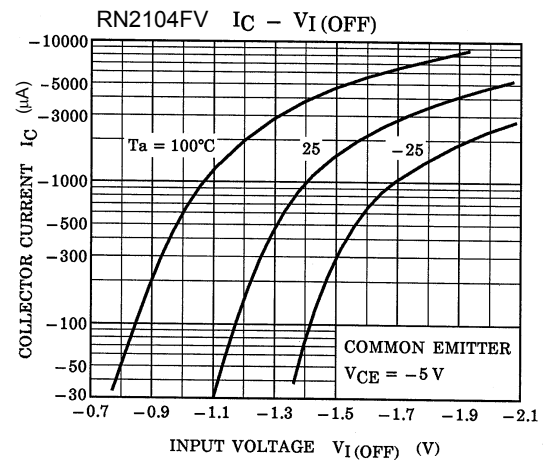
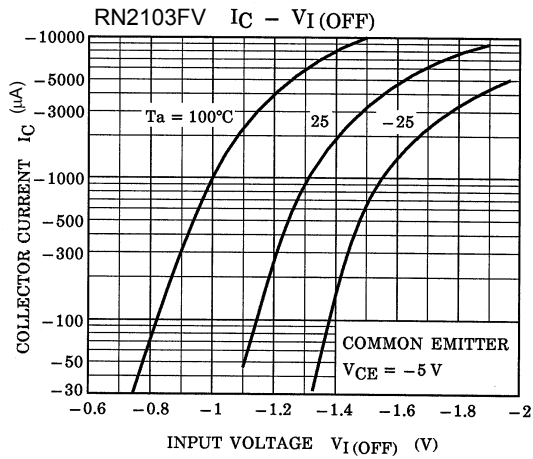
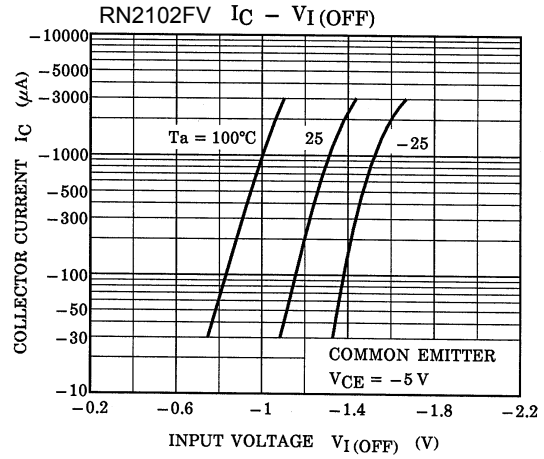
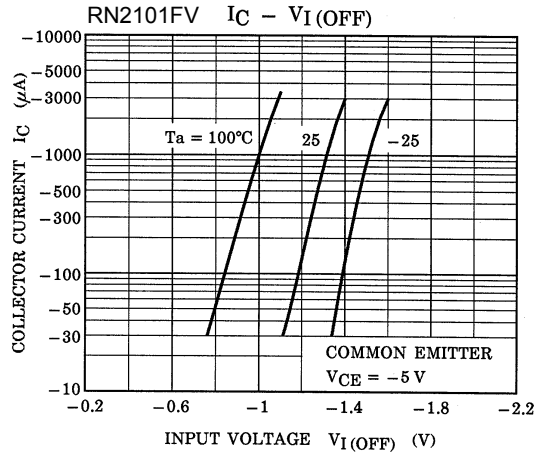
Note: Mounted on FR4 board (25.4 mm × 25.4 mm × 1.6 mm)

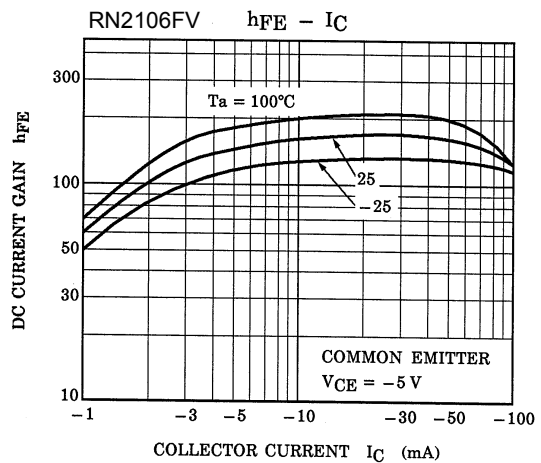
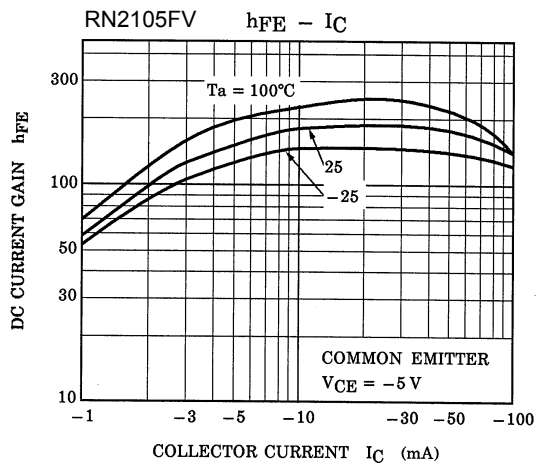
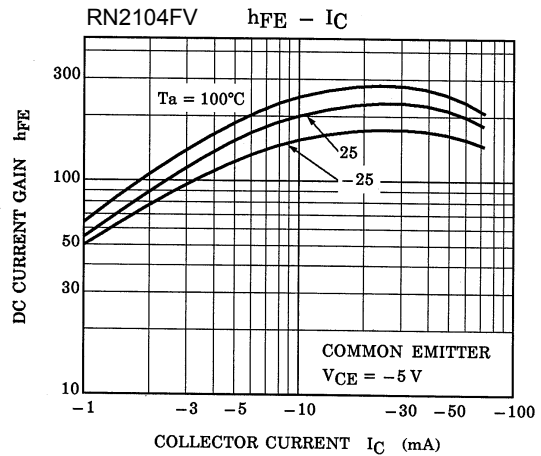
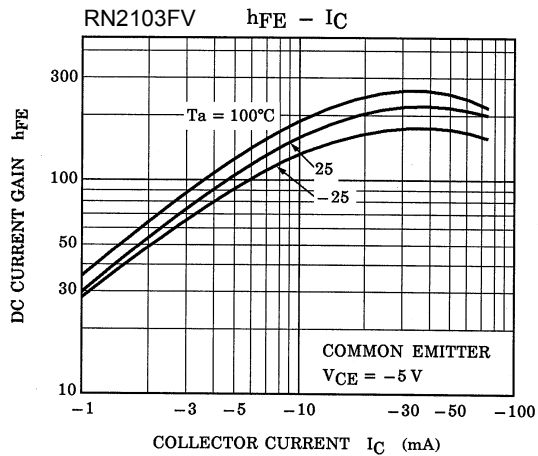
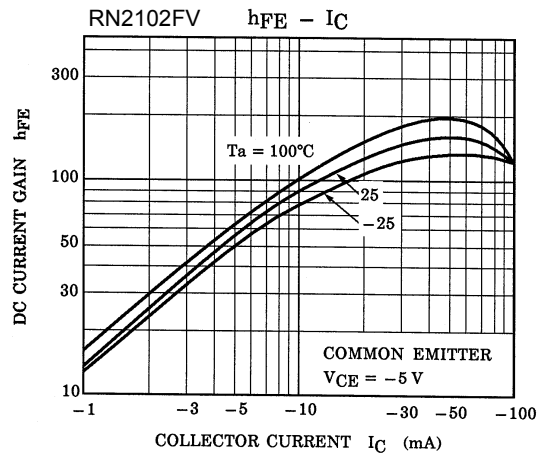
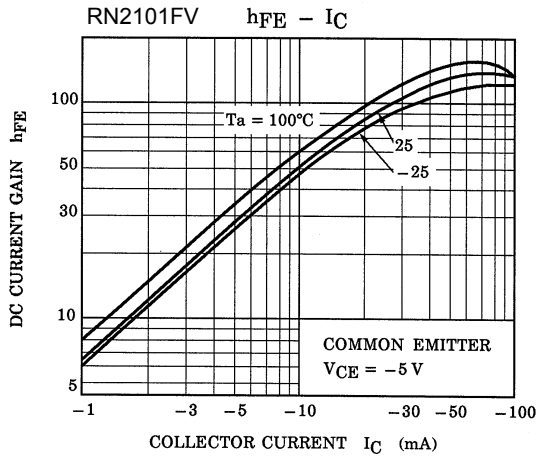


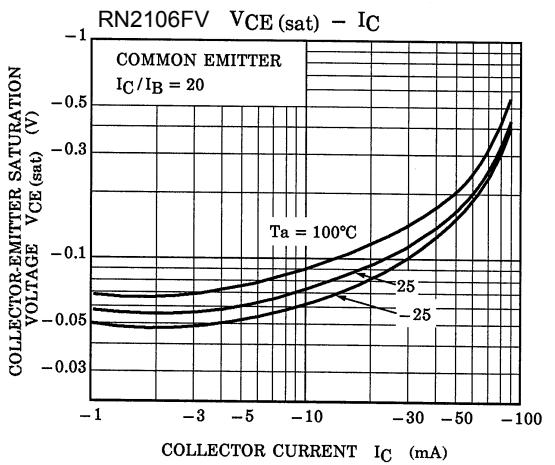
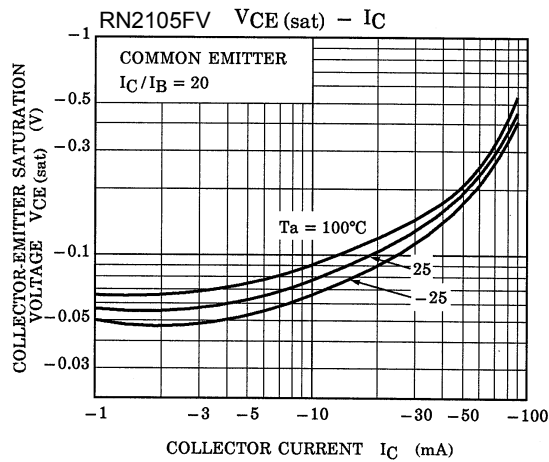
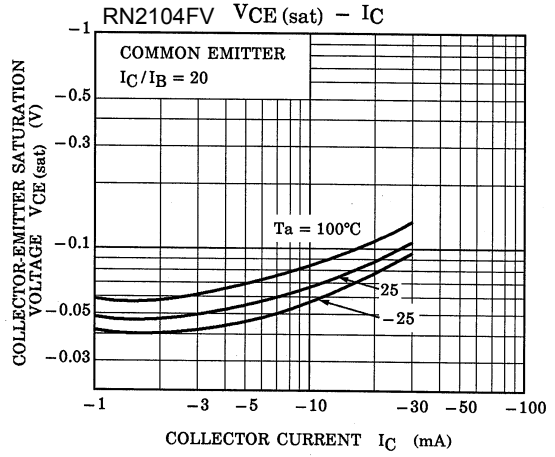
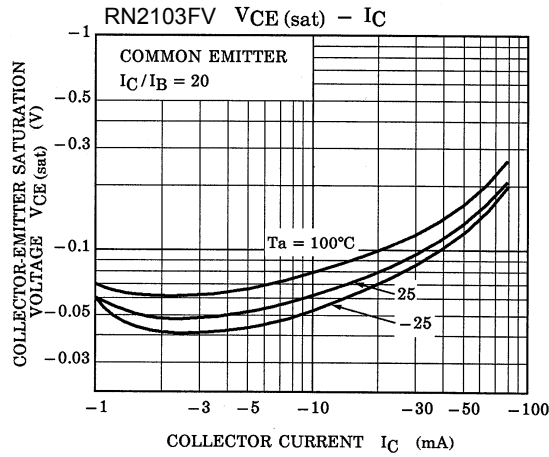
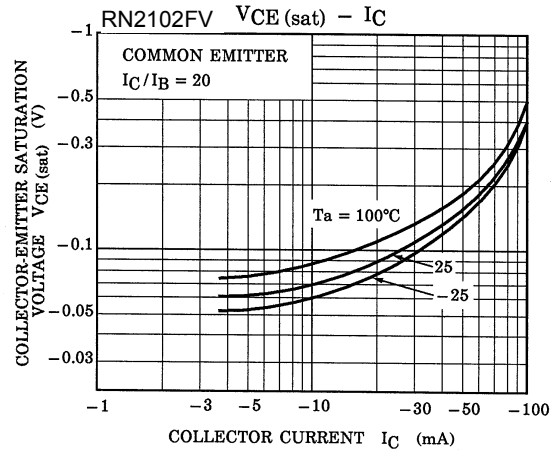
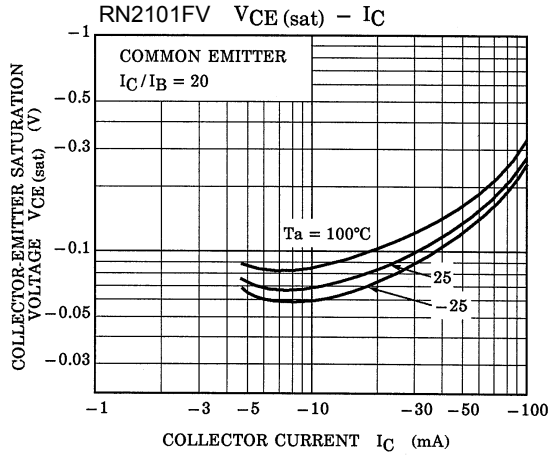
Electrical Characteristics (Ta = 25°C)

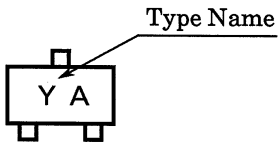
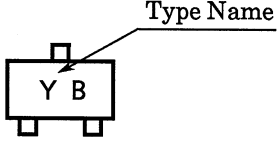
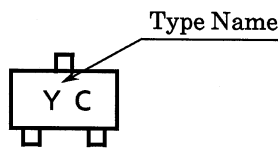
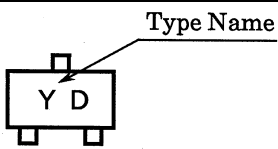
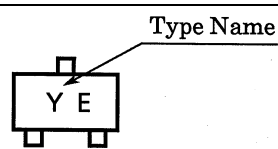
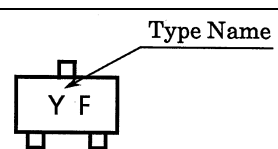
Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2101FV~2106FV	I_{CBO}	—	$V_{CB} = -50V, I_E = 0$	—	—	-100	nA
		I_{CEO}		$V_{CE} = -50V, I_B = 0$	—	—	-500	
Emitter cut-off current	RN2101FV	I_{EBO}	—	$V_{EB} = -10V, I_C = 0$	-0.82	—	-1.52	mA
	RN2102FV				-0.38	—	-0.71	
	RN2103FV				-0.17	—	-0.33	
	RN2104FV			-0.082	—	-0.15		
	RN2105FV			$V_{EB} = -5V, I_C = 0$	-0.078	—	-0.145	
	RN2106FV				-0.074	—	-0.138	
DC current gain	RN2101FV	h_{FE}	—	$V_{CE} = -5V, I_C = -10mA$	30	—	—	
	RN2102FV				50	—	—	
	RN2103FV				70	—	—	
	RN2104FV				80	—	—	
	RN2105FV				80	—	—	
	RN2106FV				80	—	—	
Collector-emitter saturation voltage	RN2101FV~2106FV	$V_{CE(sat)}$	—	$I_C = -5mA, I_B = -0.25mA$	—	-0.1	-0.3	V
Input voltage (ON)	RN2101FV	$V_{I(ON)}$	—	$V_{CE} = -0.2V, I_C = -5mA$	-1.1	—	-2.0	V
	RN2102FV				-1.2	—	-2.4	
	RN2103FV				-1.3	—	-3.0	
	RN2104FV				-1.5	—	-5.0	
	RN2105FV				-0.6	—	-1.1	
	RN2106FV				-0.7	—	-1.3	
Input voltage (OFF)	RN2101FV~2104FV	$V_{I(OFF)}$	—	$V_{CE} = -5V, I_C = -0.1mA$	-1.0	—	-1.5	V
	RN2105FV, 2106FV				-0.5	—	-0.8	
Transition frequency	RN2101FV~2106FV	f_T	—	$V_{CE} = -10V, I_C = -5mA$	—	200	—	MHz
Collector output capacitance	RN2101FV~2106FV	C_{ob}	—	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	3	—	pF
Input resistor	RN2101FV	R1	—		3.29	4.7	6.11	kΩ
	RN2102FV				7	10	13	
	RN2103FV				15.4	22	28.6	
	RN2104FV				32.9	47	61.1	
	RN2105FV				1.54	2.2	2.86	
	RN2106FV				3.29	4.7	6.11	
Resistor ratio	RN2101FV~2104FV	R1/R2	—		0.9	1.0	1.1	
	RN2105FV				0.0421	0.0468	0.0515	
	RN2106FV				0.09	0.1	0.11	









Type Name	Marking
RN2101FV	
RN2102FV	
RN2103FV	
RN2104FV	
RN2105FV	
RN2106FV	

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